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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

•XF

Product Status	Obsolete
Core Processor	PIC
Core Size	8-Bit
Speed	10MHz
Connectivity	I <sup>2</sup> C, SPI
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	16
Program Memory Size	1.75КВ (1К х 14)
Program Memory Type	FLASH
EEPROM Size	128 x 8
RAM Size	128 x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 5.5V
Data Converters	A/D 5x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-VQFN Exposed Pad
Supplier Device Package	28-QFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic16lf818-i-mltsl

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong





### FIGURE 2-4: PIC16F819 REGISTER FILE MAP

ŀ	File Address		File Address	ļ	File Address	А	Fi dd
Indirect addr.(*)	00h	Indirect addr.(*)	80h	Indirect addr.(*)	100h	Indirect addr.(*)	18
TMR0	01h	OPTION_REG	81h	TMR0	101h	OPTION_REG	18
PCL	02h	PCL	82h	PCL	102h	PCL	1
STATUS	03h	STATUS	83h	STATUS	103h	STATUS	1
FSR	04h	FSR	84h	FSR	104h	FSR	1
PORTA	05h	TRISA	85h		105h		1
PORTB	06h	TRISB	86h	PORTB	106h	TRISB	1
	07h		87h		107h		1
	08h		88h		108h		18
	09h		89h		109h		18
PCLATH	0Ah	PCLATH	8Ah	PCLATH	10Ah	PCLATH	18
INTCON	0Bh	INTCON	8Bh	INTCON	10Bh	INTCON	18
PIR1	0Ch	PIE1	8Ch	EEDATA	10Ch	EECON1	18
PIR2	0Dh	PIE2	8Dh	EEADR	10Dh	EECON2	18
TMR1L	0Eh	PCON	8Eh	EEDATH	10Eh	Reserved <sup>(1)</sup>	18
TMR1H	0Fh	OSCCON	8Fh	EEADRH	10Fh	Reserved <sup>(1)</sup>	18
T1CON	10h	OSCTUNE	90h		110h		19
TMR2	11h		91h				
T2CON	12h	PR2	92h				
SSPBUE	13h	SSPADD	93h				
SSPCON	14n	SSPSTAT	94h				
	15h		95h				
	160		96h				
CCP1CON	170		97h				
	18n 10h		98h				
	1911		99n				
	1 A II 1 B b		9An ODh				
	101 10b		9BN				
			901 00b				
	1Eh	ADRESI					
	1Fh		9En 9Fh		11Fh		19
ADCONU	20h				120h		1.
	2011		AUN				
General		General		General			
Purpose		Register		Register		Accesses	
Register		80 Bytes		80 Bytes		20h-7Fh	
96 Bytes				,			
		<b>A a a a a a a a a a a</b>	EFh	A.0000000	16Fh		
		ACCESSES 70h-7Fh	FUN	70h-7Fh			
Bank 0	J 7Fh	Rank 1	FFh	Bank 2	17Fh	Rank 3	1
Dalik U		Dalik I		Dank Z		Dank J	

### 2.2.2.4 PIE1 Register

This register contains the individual enable bits for the peripheral interrupts.

Note:	Bit PEIE (INTCON<6>) must be set to
	enable any peripheral interrupt.

-n = Value at POR

# REGISTER 2-4: PIE1: PERIPHERAL INTERRUPT ENABLE REGISTER 1 (ADDRESS 8Ch)

	U-0	R/W-0	U-0	U-0	R/W-0	R/W-0	R/W-0	, R/W-0
	—	ADIE	—	—	SSPIE	CCP1IE	TMR2IE	TMR1IE
	bit 7						. <u> </u>	bit 0
bit 7	Unimplem	ented: Read	<b>d as</b> '0'					
bit 6	ADIE: A/D	Converter Ir	nterrupt Enat	ole bit				
	1 = Enable 0 = Disabl	es the A/D co	onverter inter converter inte	rrupt Prrupt				
bit 5-4	Unimplem	ented: Read	<b>d as</b> '0'					
bit 3	SSPIE: Syr	nchronous S	Serial Port Int	errupt Enable	ə bit			
	1 = Enable 0 = Disabl	es the SSP in the SSP in the SSP	nterrupt interrupt					
bit 2	CCP1IE: C	CP1 Interru	pt Enable bit					
	<ul> <li>1 = Enables the CCP1 interrupt</li> <li>0 = Disables the CCP1 interrupt</li> </ul>							
bit 1	TMR2IE: T	MR2 to PR2	2 Match Inter	rupt Enable k	bit			
	<ul> <li>1 = Enables the TMR2 to PR2 match interrupt</li> <li>0 = Disables the TMR2 to PR2 match interrupt</li> </ul>							
bit 0	TMR1IE: T	MR1 Overflo	ow Interrupt I	Enable bit				
	1 = Enable	es the TMR1	overflow int	errupt				
	0 = Disable	es the TMR	1 overflow int	terrupt				
	Legend:							
	R = Read	able bit	W = W	Vritable bit	U = Unin	nplemented	bit, read as	'0'

'1' = Bit is set

'0' = Bit is cleared

x = Bit is unknown

#### 2.2.2.6 **PIE2** Register

The PIE2 register contains the individual enable bit for the EEPROM write operation interrupt.

#### **REGISTER 2-6:** PIE2: PERIPHERAL INTERRUPT ENABLE REGISTER 2 (ADDRESS 8Dh)

	U-0	U-0	U-0	R/W-0	U-0	U-0	U-0	U-0
		—	—	EEIE	—		—	—
	bit 7							bit 0
bit 7-5	Unimplem	ented: Read	<b>d as</b> '0'					
bit 4	EEIE: EEP	ROM Write	Operation Ir	terrupt Enal	ole bit			
	1 = Enable 0 = Disable	EE write int	errupt terrupt					
bit 3-0	Unimplem	ented: Read	<b>d as</b> '0'					
	Legend:							
	R = Reada	ble bit	W = W	ritable bit	U = Unim	plemented	bit_read.as.'(	0'

#### 2.2.2.7 **PIR2** Register

The PIR2 register contains the flag bit for the EEPROM write operation interrupt.

-n = Value at POR

Note:	Interrupt flag bits are set when an interrupt
	condition occurs regardless of the state of
	its corresponding enable bit or the Global
	Interrupt Enable bit, GIE (INTCON<7>).
	User software should ensure the appropri-
	ate interrupt flag bits are clear prior to
	enabling an interrupt.

x = Bit is unknown

'0' = Bit is cleared

#### **REGISTER 2-7:** PIR2: PERIPHERAL INTERRUPT REQUEST (FLAG) REGISTER 2 (ADDRESS 0Dh)

'1' = Bit is set

					<b>b</b> : (: <b>b</b> : ( <b>b</b> )		(/ .= =	
	U-0	U-0	U-0	R/W-0	U-0	U-0	U-0	U-0
		—	_	EEIF	—	_	—	_
	bit 7							bit 0
bit 7-5	Unimplem	ented: Rea	<b>d as</b> '0'					
bit 4	EEIF: EEP	ROM Write	Operation Ir	nterrupt Enal	ble bit			
	1 = Enable 0 = Disable	e EE write int e EE write in	errupt terrupt					
bit 3-0	Unimplem	ented: Rea	<b>d as</b> '0'					
	Legend:							

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented	bit, read as '0'
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown

# 3.7 Writing to Flash Program Memory

Flash program memory may only be written to if the destination address is in a segment of memory that is not write-protected, as defined in bits WRT1:WRT0 of the device Configuration Word (Register 12-1). Flash program memory must be written in four-word blocks. A block consists of four words with sequential addresses, with a lower boundary defined by an address, where EEADR<1:0> = 00. At the same time, all block writes to program memory are done as write-only operations. The program memory must first be erased. The write operation is edge-aligned and cannot occur across boundaries.

To write to the program memory, the data must first be loaded into the buffer registers. There are four 14-bit buffer registers and they are addressed by the low 2 bits of EEADR.

The following sequence of events illustrate how to perform a write to program memory:

- Set the EEPGD and WREN bits in the EECON1 register
- Clear the FREE bit in EECON1
- Write address to EEADRH:EEADR
- Write data to EEDATH:EEDATA
- Write 55 to EECON2
- Write AA to EECON2
- Set WR bit in EECON 1

The user must follow the same specific sequence to initiate the write for each word in the program block by writing each program word in sequence (00, 01, 10, 11).

There are 4 buffer register words and all four locations **MUST** be written to with correct data.

After the "BSF EECON1, WR" instruction, if EEADR  $\neq$  xxxxx11, then a short write will occur. This short write-only transfers the data to the buffer register. The WR bit will be cleared in hardware after one cycle.

After the "BSF EECON1, WR" instruction, if EEADR = xxxxx11, then a long write will occur. This will simultaneously transfer the data from EEDATH:EEDATA to the buffer registers and begin the write of all four words. The processor will execute the next instruction and then ignore the subsequent instruction. The user should place NOP instructions into the second words. The processor will then halt internal operations for typically 2 msec in which the write takes place. This is not a Sleep mode, as the clocks and peripherals will continue to run. After the write cycle, the processor will resume operation with the 3rd instruction after the EECON1 write instruction.

After each long write, the 4 buffer registers will be reset to 3FFF.



#### FIGURE 3-1: BLOCK WRITES TO FLASH PROGRAM MEMORY

# 4.0 OSCILLATOR CONFIGURATIONS

## 4.1 Oscillator Types

The PIC16F818/819 can be operated in eight different oscillator modes. The user can program three configuration bits (FOSC2:FOSC0) to select one of these eight modes (modes 5-8 are new PIC16 oscillator configurations):

- 1. LP Low-Power Crystal
- 2. XT Crystal/Resonator
- 3. HS High-Speed Crystal/Resonator
- 4. RC External Resistor/Capacitor with Fosc/4 output on RA6
- 5. RCIO External Resistor/Capacitor with I/O on RA6
- 6. INTIO1 Internal Oscillator with Fosc/4 output on RA6 and I/O on RA7
- 7. INTIO2 Internal Oscillator with I/O on RA6 and RA7
- 8. ECIO External Clock with I/O on RA6

# 4.2 Crystal Oscillator/Ceramic Resonators

In XT, LP or HS modes, a crystal or ceramic resonator is connected to the OSC1/CLKI and OSC2/CLKO pins to establish oscillation (see Figure 4-1 and Figure 4-2). The PIC16F818/819 oscillator design requires the use of a parallel cut crystal. Use of a series cut crystal may give a frequency out of the crystal manufacturer's specifications.





### TABLE 4-1: CAPACITOR SELECTION FOR CRYSTAL OSCILLATOR (FOR DESIGN GUIDANCE ONLY)

Osc Type	Crystal	Typical Capacitor Values Tested:			
	Fieq	C1	C2		
LP	32 kHz	33 pF	33 pF		
	200 kHz	15 pF	15 pF		
XT	200 kHz	56 pF	56 pF		
	1 MHz	15 pF	15 pF		
	4 MHz	15 pF	15 pF		
HS	4 MHz	15 pF	15 pF		
	8 MHz	15 pF	15 pF		
	20 MHz	15 pF	15 pF		

#### Capacitor values are for design guidance only.

These capacitors were tested with the crystals listed below for basic start-up and operation. These values were not optimized.

Different capacitor values may be required to produce acceptable oscillator operation. The user should test the performance of the oscillator over the expected VDD and temperature range for the application.

See the notes following this table for additional information.

- Note 1: Higher capacitance increases the stability of the oscillator but also increases the start-up time.
  - 2: Since each crystal has its own characteristics, the user should consult the crystal manufacturer for appropriate values of external components.
  - **3:** Rs may be required in HS mode, as well as XT mode, to avoid overdriving crystals with low drive level specification.
  - **4:** Always verify oscillator performance over the VDD and temperature range that is expected for the application.

## 7.5 Timer1 Operation in Asynchronous Counter Mode

If control bit,  $\overline{\text{T1SYNC}}$  (T1CON<2>), is set, the external clock input is not synchronized. The timer continues to increment asynchronous to the internal phase clocks. The timer will continue to run during Sleep and can generate an interrupt on overflow that will wake-up the processor. However, special precautions in software are needed to read/write the timer.

In Asynchronous Counter mode, Timer1 cannot be used as a time base for capture or compare operations.

### 7.5.1 READING AND WRITING TIMER1 IN ASYNCHRONOUS COUNTER MODE

Reading TMR1H or TMR1L while the timer is running from an external asynchronous clock will ensure a valid read (taken care of in hardware). However, the user should keep in mind that reading the 16-bit timer in two 8-bit values itself poses certain problems, since the timer may overflow between the reads.

For writes, it is recommended that the user simply stop the timer and write the desired values. A write contention may occur by writing to the timer registers while the register is incrementing. This may produce an unpredictable value in the timer register.

Reading the 16-bit value requires some care. The example codes provided in Example 7-1 and Example 7-2 demonstrate how to write to and read Timer1 while it is running in Asynchronous mode.

<b>FXAMPI F 7-1</b> .	WRITING & 16-BIT FREE BUINN	ING TIMER
EARIVIFLE (-I.	WATTING A TO-DIT FREE AUNIN	

#### EXAMPLE 7-2: READING A 16-BIT FREE RUNNING TIMER

; All interrupts are	disabled
MOVF TMR1H, W	; Read high byte
MOVWF TMPH	
MOVF TMR1L, W	; Read low byte
MOVWF TMPL	
MOVF TMR1H, W	; Read high byte
SUBWF TMPH, W	; Sub 1st read with 2nd read
BTFSC STATUS, Z	; Is result = 0
GOTO CONTINUE	; Good 16-bit read
; TMR1L may have rol	led over between the read of the high and low bytes.
; Reading the high a	nd low bytes now will read a good value.
MOVF TMR1H, W	; Read high byte
MOVWF TMPH	
MOVF TMR1L, W	; Read low byte
MOVWF TMPL	; Re-enable the Interrupt (if required)
CONTINUE	; Continue with your code

# 9.0 CAPTURE/COMPARE/PWM (CCP) MODULE

The Capture/Compare/PWM (CCP) module contains a 16-bit register that can operate as a:

- 16-bit Capture register
- 16-bit Compare register
- PWM Master/Slave Duty Cycle register

Table 9-1 shows the timer resources of the CCP module modes.

Capture/Compare/PWM Register 1 (CCPR1) is comprised of two 8-bit registers: CCPR1L (low byte) and CCPR1H (high byte). The CCP1CON register controls the operation of CCP1. The special event trigger is generated by a compare match which will reset Timer1 and start an A/D conversion (if the A/D module is enabled). The CCP module's input/output pin (CCP1) can be configured as RB2 or RB3. This selection is set in bit 12 (CCPMX) of the Configuration Word register.

Additional information on the CCP module is available in the "PIC<sup>®</sup> Mid-Range MCU Family Reference Manual" (DS33023) and in Application Note AN594, "Using the CCP Module(s)" (DS00594).

### TABLE 9-1: CCP MODE – TIMER RESOURCE

CCP Mode	Timer Resource
Capture Compare	Timer1 Timer1
PWM	Timer2

### **REGISTER 9-1:** CCP1CON: CAPTURE/COMPARE/PWM CONTROL REGISTER 1 (ADDRESS 17h)

							•	,			
	U-0	U-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0			
	—	_	CCP1X	CCP1Y	CCP1M3	CCP1M2	CCP1M1	CCP1M0			
	bit 7							bit 0			
bit 7-6	Unimpleme	ented: Read	<b>as</b> '0'								
bit 5-4	CCP1X:CCP1Y: PWM Least Significant bits										
	Capture mode: Unused.										
	<u>Compare m</u> Unused.	node:									
	<u>PWM mode</u> These bits a	<u>»:</u> are the two l	LSbs of the	PWM duty	cycle. The e	eight MSbs a	re found in (	CCPRxL.			
bit 3-0	CCP1M3:CCP1M0: CCP1 Mode Select bits										
	0000 = Capture/Compare/PWM disabled (resets CCP1 module)										
	0100 = Cap	oture mode,	every fallin	g edge							
	0101 = Cap	oture mode,	every rising	g edge							
	0110 = Cap	oture mode,	every 4th r	ising edge							
	0111 = Cap	oture mode,	every 16th	rising edge		in ant)					
	1000 = Cor	mpare mode	, sei ouipui , clear outr	ut on mate		it is set)					
	1010 = Compare mode, generate software interrupt on match (CCP1IF bit is set, CCP1 pin is unaffected)										
	1011 = Compare mode, trigger special event (CCP1IF bit is set, CCP1 pin is unaffe CCP1 resets TMR1 and starts an A/D conversion (if A/D module is enabled)										
	11xx = PW	/M mode									
	Legend:										
	R = Reada	ble bit	W = V	Vritable bit	U = Uni	implemented	bit, read as	; '0'			
	-n = Value	at POR	'1' = E	Bit is set	'0' = Bit	is cleared	x = Bit is	unknown			

#### **FIGURE 12-9:** WAKE-UP FROM SLEEP THROUGH INTERRUPT

Q1  Q2   Q3   Q OSC1 ////// CLKO <sup>(4)</sup> //	24; Q1 Q2 Q3 Q4; \_'/\_/\_/	Q1	Tost <sup>(2)</sup>	Q1 Q2 Q3 Q4 ////////	; Q1 Q2 Q3 Q4 ;////////////////////////////////////	Q1 Q2 Q3 Q4 ////////////////////////////////////	Q1 Q2 Q3 Q4;
INI pin	<u> </u>		1 1 1 1		<u>1</u> 1	I <u> </u>	
INTF Flag (INTCON<1>)		Y	· · · ·		Interrupt Latency		
GIE bit (INTCON<7>)		Processor in					
INSTRUCTION FLOW					I I		I I
PC Y PC	X PC + 1	X PC +	- 2	PC + 2	X PC + 2	X 0004h	X 0005h
Instruction Fetched { Inst(PC) = Slee	ep Inst(PC + 1)		1	Inst(PC + 2)	1	Inst(0004h)	Inst(0005h)
Instruction $\begin{cases} I & Inst(PC - 1) \\ Inst(PC - 1) \end{cases}$	Sleep			Inst(PC + 1)	Dummy Cycle	Dummy Cycle	Inst(0004h)
Note 1: XT HS or I P Osc	illator mode assumed	4					

2: TOST = 1024 TOSC (drawing not to scale). This delay will not be there for RC Oscillator mode.

GIE = 1 assumed. In this case, after wake-up, the processor jumps to the interrupt routine. If GIE = 0, execution will continue in-line. 3:

4: CLKO is not available in these oscillator modes but shown here for timing reference.

### 12.14 In-Circuit Debugger

When the DEBUG bit in the Configuration Word is programmed to a '0', the In-Circuit Debugger functionality is enabled. This function allows simple debugging functions when used with MPLAB® ICD. When the microcontroller has this feature enabled, some of the resources are not available for general use. Table 12-6 shows which features are consumed by the background debugger.

TABLE 12-6: DEBUGGER RESOL	URCES
----------------------------	-------

I/O pins	RB6, RB7
Stack	1 level
Program Memory	Address 0000h must be NOP
	Last 100h words
Data Memory	0x070 (0x0F0, 0x170, 0x1F0) 0x1EB-0x1EF

To use the In-Circuit Debugger function of the microcontroller, the design must implement In-Circuit Serial Programming connections to MCLR/VPP, VDD, GND, RB7 and RB6. This will interface to the in-circuit debugger module available from Microchip or one of the third party development tool companies.

# 12.15 Program Verification/Code Protection

If the code protection bit(s) have not been programmed, the on-chip program memory can be read out for verification purposes.

### 12.16 ID Locations

Four memory locations (2000h-2003h) are designated as ID locations, where the user can store checksum or other code identification numbers. These locations are not accessible during normal execution but are readable and writable during program/verify. It is recommended that only the four Least Significant bits of the ID location are used.

# **15.0 ELECTRICAL CHARACTERISTICS**

# Absolute Maximum Ratings †

Ambient temperature under bias	40°C to +125°C
Storage temperature	65°C to +150°C
Voltage on any pin with respect to Vss (except VDD and $\overline{MCLR}$ )	-0.3V to (VDD + 0.3V)
Voltage on VDD with respect to Vss	-0.3 to +7.5V
Voltage on MCLR with respect to Vss (Note 2)	-0.3 to +14V
Total power dissipation (Note 1)	1W
Maximum current out of Vss pin	
Maximum current into Vod pin	
Input clamp current, Iк (Vi < 0 or Vi > VDD)	±20 mA
Output clamp current, Ioк (Vo < 0 or Vo > VDD)	±20 mA
Maximum output current sunk by any I/O pin	25 mA
Maximum output current sourced by any I/O pin	25 mA
Maximum current sunk by PORTA	
Maximum current sourced by PORTA	
Maximum current sunk by PORTB	
Maximum current sourced by PORTB	
<b>Note 1:</b> Power dissipation is calculated as follows: Pdis = VDD x {IDD $-\Sigma$ IOH} + $\Sigma$ {(	$VDD - VOH$ ) x IOH} + $\Sigma$ (VOL x IOL)
<ol> <li>Voltage spikes at the MCLR pin may cause latch-up. A series resistor of g to pull MCLR to VDD, rather than tying the pin directly to VDD.</li> </ol>	reater than 1 k $\Omega$ should be used

† NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

# 15.2 DC Characteristics: Power-Down and Supply Current PIC16F818/819 (Industrial, Extended) PIC16LF818/819 (Industrial) (Continued)

PIC16LF8 (Indus	<b>818/819</b> strial)	Standard Operating Conditions (unless otherwise stated)Operating temperature $-40^{\circ}C \le TA \le +85^{\circ}C$ for industrial							
PIC16F8 <sup>4</sup> (Indus	<b>18/819</b> strial, Extended)	<b>Standa</b> Operati	rd Oper	ating Co erature	onditions (unless -40°C ≤ TA -40°C ≤ TA	s otherwise states $\leq$ +85°C for indus $\leq$ +125°C for exte	t) trial nded		
Param No.	Device	Тур	Max	Units	its Conditions				
	Supply Current (IDD) <sup>(2,3)</sup>								
	PIC16LF818/819	9	20	μΑ	-40°C		Fosc = 32 kHz (LP Oscillator)		
		7	15	μA	+25°C	VDD = 2.0V			
		7	15	μA	+85°C				
	PIC16LF818/819	16	30	μA	-40°C				
		14	25	μA	+25°C	VDD = 3.0V			
		14	25	μA	+85°C	Vdd = 5.0V			
	All devices	32	40	μA	-40°C				
		26	35	μA	+25°C				
		26	35	μA	+85°C				
	Extended devices	35	53	μA	+125°C				

**Legend:** Shading of rows is to assist in readability of the table.

**Note 1:** The power-down current in Sleep mode does not depend on the oscillator type. Power-down current is measured with the part in Sleep mode, with all I/O pins in high-impedance state and tied to VDD or VSS and all features that add delta current disabled (such as WDT, Timer1 Oscillator, BOR, etc.).

2: The supply current is mainly a function of operating voltage, frequency and mode. Other factors, such as I/O pin loading and switching rate, oscillator type and circuit, internal code execution pattern and temperature, also have an impact on the current consumption.

The test conditions for all IDD measurements in active operation mode are:

OSC1 = external square wave, from rail-to-rail; all I/O pins tri-stated, pulled to VDD;

MCLR = VDD; WDT enabled/disabled as specified.

3: For RC oscillator configurations, current through REXT is not included. The current through the resistor can be estimated by the formula Ir = VDD/2REXT (mA) with REXT in k $\Omega$ .

# 15.2 DC Characteristics: Power-Down and Supply Current PIC16F818/819 (Industrial, Extended) PIC16LF818/819 (Industrial) (Continued)

PIC16LF (Indus	<b>818/819</b> strial)	Standard Operating Conditions (unless otherwise stated)Operating temperature $-40^{\circ}C \le TA \le +85^{\circ}C$ for industrial							
PIC16F8 <sup>.</sup> (Indus							<b>I)</b> irial nded		
Param No.	Device	Тур	Max	Units	Conditions				
	Supply Current (IDD) <sup>(2,3)</sup>								
	PIC16LF818/819	72	95	μΑ	-40°C				
		76	90	μΑ	+25°C	VDD = 2.0V			
		76	90	μΑ	+85°C				
	PIC16LF818/819	138	175	μΑ	-40°C		Fosc = 1 MHz (RC Oscillator) <sup>(3)</sup>		
		136	170	μΑ	+25°C	VDD = 3.0V			
		136	170	μΑ	+85°C				
	All devices	310	380	μΑ	-40°C				
		290	360	μΑ	+25°C	Vpp = 5.0V			
		280	360	μΑ	+85°C	VDD = 3.0V			
	Extended devices	350	500	μΑ	+125°C				
	PIC16LF818/819	270	315	μΑ	-40°C				
		280	310	μΑ	+25°C	VDD = 2.0V			
		285	310	μΑ	+85°C				
	PIC16LF818/819	460	610	μΑ	-40°C				
		450	600	μΑ	+25°C	VDD = 3.0V (RC Osci	Fosc = 4 MHz		
		450	600	μΑ	+85°C		(RC Oscillator) <sup>(3)</sup>		
	All devices	900	1060	μΑ	-40°C				
		890	1050	μΑ	+25°C				
		890	1050	μΑ	+85°C	VDD - 3.0V			
	Extended devices	.920	1.5	mA	+125°C	1			

Legend: Shading of rows is to assist in readability of the table.

**Note 1:** The power-down current in Sleep mode does not depend on the oscillator type. Power-down current is measured with the part in Sleep mode, with all I/O pins in high-impedance state and tied to VDD or VSs and all features that add delta current disabled (such as WDT, Timer1 Oscillator, BOR, etc.).

2: The supply current is mainly a function of operating voltage, frequency and mode. Other factors, such as I/O pin loading and switching rate, oscillator type and circuit, internal code execution pattern and temperature, also have an impact on the current consumption.

The test conditions for all IDD measurements in active operation mode are:

OSC1 = external square wave, from rail-to-rail; all I/O pins tri-stated, pulled to VDD;

- MCLR = VDD; WDT enabled/disabled as specified.
- **3:** For RC oscillator configurations, current through REXT is not included. The current through the resistor can be estimated by the formula Ir = VDD/2REXT (mA) with REXT in kΩ.

# 15.2 DC Characteristics: Power-Down and Supply Current PIC16F818/819 (Industrial, Extended) PIC16LF818/819 (Industrial) (Continued)

PIC16LF8 (Indus	<b>318/819</b> strial)	Standard Operating Conditions (unless otherwise stated)Operating temperature $-40^{\circ}C \le TA \le +85^{\circ}C$ for industrial							
PIC16F81 (Indus	18/819 strial, Extended)	$\begin{tabular}{lllllllllllllllllllllllllllllllllll$					<b>t)</b> trial nded		
Param No.	Device	Тур	Max	Units	Conditions				
	Supply Current (IDD) <sup>(2,3)</sup>	)							
	All devices	1.8	2.3	mA	-40°C				
		1.6	2.2	mA	+25°C	VDD = 4.0V			
		1.3	2.2	mA	+85°C				
	All devices	3.0	4.2	mA	-40°C	FOSC = 20 MF (HS Oscillato	FOSC = 20 MHZ (HS Oscillator)		
		2.5	4.0	mA	+25°C		(no oscillator)		
		2.5	4.0	mA	+85°C	vuu ≅ 5.0v			
	Extended devices	3.0	5.0	mA	+125°C				

Legend: Shading of rows is to assist in readability of the table.

**Note 1:** The power-down current in Sleep mode does not depend on the oscillator type. Power-down current is measured with the part in Sleep mode, with all I/O pins in high-impedance state and tied to VDD or VSS and all features that add delta current disabled (such as WDT, Timer1 Oscillator, BOR, etc.).

2: The supply current is mainly a function of operating voltage, frequency and mode. Other factors, such as I/O pin loading and switching rate, oscillator type and circuit, internal code execution pattern and temperature, also have an impact on the current consumption.

The test conditions for all IDD measurements in active operation mode are:

 $\frac{OSC1}{MCLR}$  = external square wave, from rail-to-rail; all I/O pins tri-stated, pulled to VDD;  $\frac{MCLR}{MCLR}$  = VDD; WDT enabled/disabled as specified.

**3:** For RC oscillator configurations, current through REXT is not included. The current through the resistor can be estimated by the formula Ir = VDD/2REXT (mA) with REXT in kΩ.

FIGURE 16-7: TYPICAL IDD vs. VDD, -40°C TO +125°C, 1 MHz TO 8 MHz (RC\_RUN MODE, ALL PERIPHERALS DISABLED)



FIGURE 16-8: MAXIMUM IDD vs. VDD, -40°C TO +125°C, 1 MHz TO 8 MHz (RC\_RUN MODE, ALL PERIPHERALS DISABLED)





FIGURE 16-17: TYPICAL, MINIMUM AND MAXIMUM VOH vs. IOH (VDD = 5V, -40°C TO +125°C)





NOTES:

# 18-Lead Plastic Small Outline (SO) - Wide, 7.50 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





Microchip Technology Drawing C04-051C Sheet 1 of 2

# APPENDIX A: REVISION HISTORY

## Revision A (May 2002)

Original version of this data sheet.

# **Revision B (August 2002)**

Added INTRC section. PWRT and BOR are independent of each other. Revised program memory text and code routine. Added QFN package. Modified PORTB diagrams.

## **Revision C (November 2002)**

Added various new feature descriptions. Added internal RC oscillator specifications. Added low-power Timer1 specifications and RTC application example.

## **Revision D (November 2003)**

Updated IRCF bit modification information and changed the INTOSC stabilization delay from 1 ms to 4 ms in Section 4.0 "Oscillator Configurations". Updated Section 12.17 "In-Circuit Serial Programming" to clarify LVP programming. In Section 15.0 "Electrical Characteristics", the DC Characteristics (Section 15.2 and Section 15.3) have been updated to include the Typ, Min and Max values and Table 15-1 "External Clock Timing Requirements" has been updated.

# **Revision E (September 2004)**

This revision includes the DC and AC Characteristics Graphs and Tables. The Electrical Specifications in Section 16.0 "DC and AC Characteristics Graphs and Tables" have been updated and there have been minor corrections to the data sheet text.

# **Revision F (November 2011)**

This revision updated **Section 17.0** "Packaging Information".

# APPENDIX B: DEVICE DIFFERENCES

The differences between the devices in this data sheet are listed in Table B-1.

#### TABLE B-1: DIFFERENCES BETWEEN THE PIC16F818 AND PIC16F819

Features	PIC16F818	PIC16F819
Flash Program Memory (14-bit words)	1K	2K
Data Memory (bytes)	128	256
EEPROM Data Memory (bytes)	128	256

NOTES:

NOTES: